

## Refine Search

10/760,358

### Search Results -

Terms	Documents
L3 and (barium adj strontium adj titanate)	3

Database:

US Pro-Grant Publication Full-Text Database  
**US Patents Full-Text Database**  
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 EPO Abstracts Database  
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 Derwent World Patents Index  
 IBM Technical Disclosure Bulletins

Search:

L5

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### Search History

 DATE: Saturday, June 26, 2004    [Printable Copy](#)    [Create Case](#)

 Set  
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 result set

DB=USPT; PLUR=YES; OP=AND

<u>L5</u>	L3 and (barium adj strontium adj titanate)	3	<u>L5</u>
<u>L4</u>	L3 and (metal near5 patterning)	6	<u>L4</u>
<u>L3</u>	L2 and refractory	21	<u>L3</u>
<u>L2</u>	L1 and (gate near electrode)	48	<u>L2</u>
<u>L1</u>	(integrated adj circuit) and (silicon adj dioxide) and (water adj vapor) and (molybdenum or tungsten) and polycrystalline	110	<u>L1</u>

END OF SEARCH HISTORY

## Hit List

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
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Search Results - Record(s) 1 through 3 of 3 returned.

☐ 1. Document ID: US 6737341 B1

L5: Entry 1 of 3

File: USPT

May 18, 2004

US-PAT-NO: 6737341

DOCUMENT-IDENTIFIER: US 6737341 B1

TITLE: Semiconductor integrated circuit device and method for manufacturing the same

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw. De
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☐ 2. Document ID: US 6593229 B1

L5: Entry 2 of 3

File: USPT

Jul 15, 2003

US-PAT-NO: 6593229

DOCUMENT-IDENTIFIER: US 6593229 B1

TITLE: Semiconductor integrated circuit device and method for manufacturing the same

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw. De
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☐ 3. Document ID: US 6482740 B2

L5: Entry 3 of 3

File: USPT

Nov 19, 2002

US-PAT-NO: 6482740

DOCUMENT-IDENTIFIER: US 6482740 B2

TITLE: Method of growing electrical conductors by reducing metal oxide film with organic compound containing -O-, -CHO, or -COOH

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw. De
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Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate OACS
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Terms	Documents
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L3 and (barium adj strontium adj titanate)	3
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## Hit List

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Search Results - Record(s) 1 through 6 of 6 returned.

☐ 1. Document ID: US 6737341 B1

L4: Entry 1 of 6

File: USPT

May 18, 2004

US-PAT-NO: 6737341

DOCUMENT-IDENTIFIER: US 6737341 B1

TITLE: Semiconductor integrated circuit device and method for manufacturing the same

Full	Title	Classification	Date	Reference	Claims	KMC	Draw De
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☐ 2. Document ID: US 6723665 B2

L4: Entry 2 of 6

File: USPT

Apr 20, 2004

US-PAT-NO: 6723665

DOCUMENT-IDENTIFIER: US 6723665 B2

TITLE: Process for manufacturing semiconductor integrated circuit device including treatment of gas used in the process

Full	Title	Classification	Date	Reference	Claims	KMC	Draw De
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☐ 3. Document ID: US 6602808 B2

L4: Entry 3 of 6

File: USPT

Aug 5, 2003

US-PAT-NO: 6602808

DOCUMENT-IDENTIFIER: US 6602808 B2

TITLE: Process for manufacturing semiconductor integrated circuit device including treatment of gas used in the process

Full	Title	Classification	Date	Reference	Claims	KMC	Draw De
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☐ 4. Document ID: US 6593229 B1

L4: Entry 4 of 6

File: USPT

Jul 15, 2003

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US-PAT-NO: 6593229

DOCUMENT-IDENTIFIER: US 6593229 P1

TITLE: Semiconductor integrated circuit device and method for manufacturing the same

Full	Title	Claims	KMC	Draw. De
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☐ 5. Document ID: US 6521550 B2

L4: Entry 5 of 6

File: USPT

Feb 18, 2003

US-PAT-NO: 6521550

DOCUMENT-IDENTIFIER: US 6521550 P2

TITLE: Process for manufacturing semiconductor integrated circuit device including treatment of gas used in the process

Full	Title	Claims	KMC	Draw. De
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☐ 6. Document ID: US 6319860 B1

L4: Entry 6 of 6

File: USPT

Nov 20, 2001

US-PAT-NO: 6319860

DOCUMENT-IDENTIFIER: US 6319860 B1

TITLE: Process for manufacturing semiconductor integrated circuit device including treatment of gas used in the process

Full	Title	Claims	KMC	Draw. De
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Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate OACS
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Terms	Documents
L3 and (merit) new terms	6

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